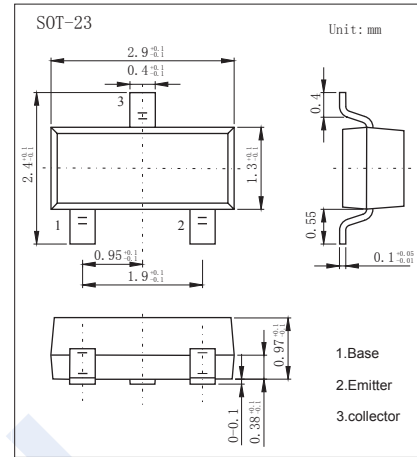


NPN Transistors

2SC4497

■ Features

- Collector Current Capability $I_c=100\text{mA}$
- Collector Emitter Voltage $V_{CE0}=300\text{V}$
- Complement to 2SA1721



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	300	V
Collector - Emitter Voltage	V_{CEO}	300	
Emitter - Base Voltage	V_{EBO}	6	
Collector Current - Continuous	I_c	100	mA
Base Current	I_B	20	
Collector Power Dissipation	P_c	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_c = 100 \mu\text{A}, I_E = 0$	300			V
Collector- emitter breakdown voltage	V_{CEO}	$I_c = 1 \text{mA}, I_B = 0$	300			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu\text{A}, I_c = 0$	6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 300 \text{V}, I_E = 0$			0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6 \text{V}, I_c = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 20 \text{mA}, I_B = 2 \text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 20 \text{mA}, I_B = 2 \text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 10 \text{V}, I_c = 20 \text{mA}$	30		150	
		$V_{CE} = 10 \text{V}, I_c = 1 \text{mA}$	20			
Collector output capacitance	C_{ob}	$V_{CB} = 20 \text{V}, I_E = 0, f = 1 \text{MHz}$			4	pF
Transition frequency	f_r	$V_{CE} = 10 \text{V}, I_c = 10 \text{mA}$		70		MHz

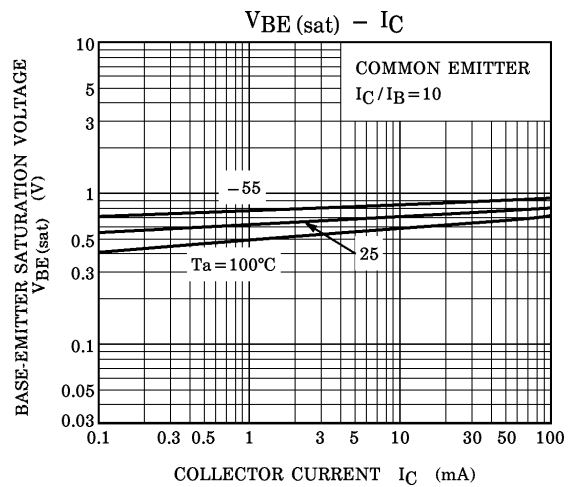
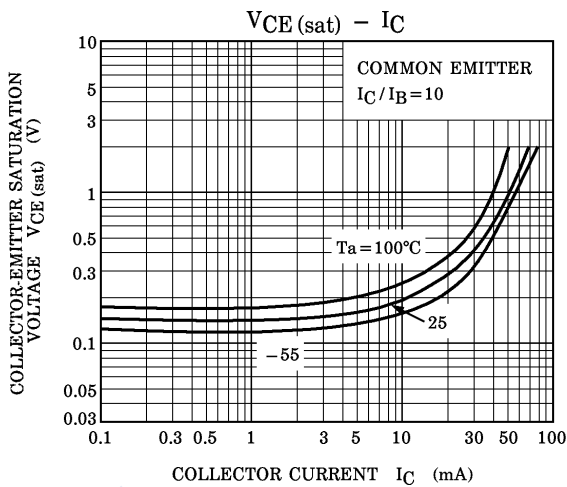
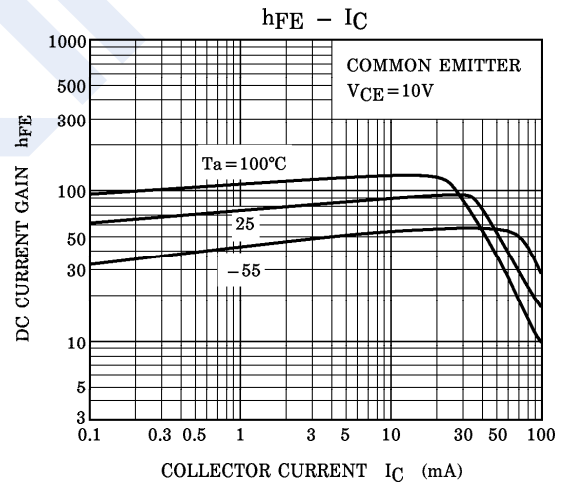
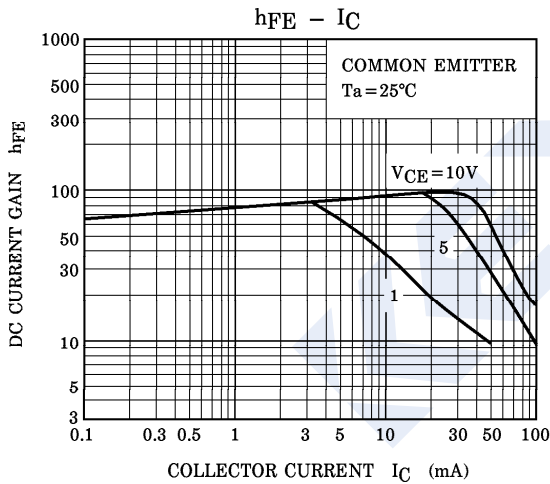
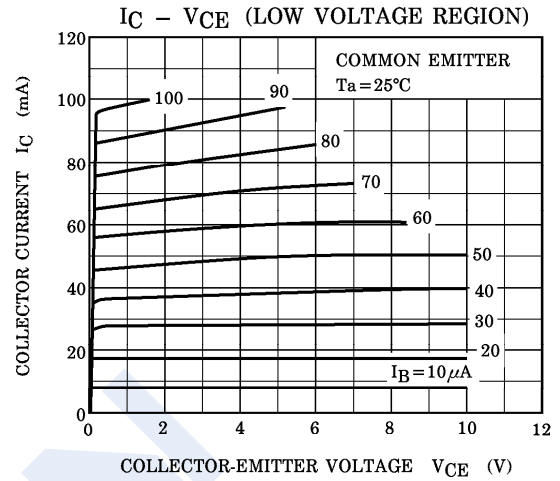
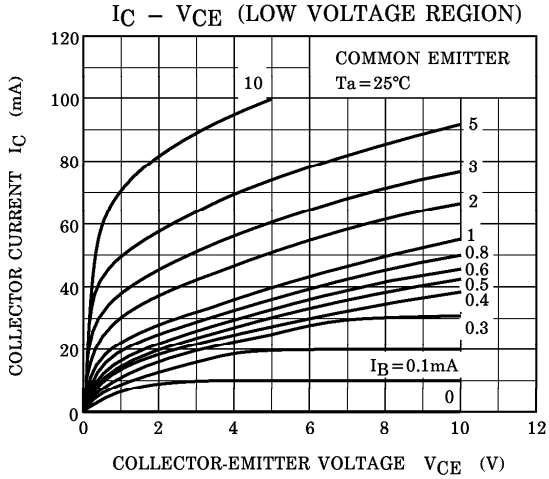
■ Classification of $h_{FE}(1)$

Type	2SC4497-R	2SC4497-O
Range	30-90	50-150
Marking	3R	3O

NPN Transistors

2SC4497

■ Typical Characteristics



NPN Transistors

2SC4497

■ Typical Characteristics

